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PTO/SB/08a/b (07-05)

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| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Use as many sheets as necessary) |   |    | Application Number       | 09/855,532-Conf. #8772 |
|   |   |    | Filing Date              | May 16, 2001           |
|   |   |    | First Named Inventor     | Joseph E. Geusic       |
|   |   |    | Art Unit                 | 2828                   |
|   |   |    | Examiner Name            | A. Rodriguez           |
|   |   |    | Attorney Docket Number   | M4065.0439/P439        |
| Sheet   | 1 | of | 1                        |                        |

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| Examiner<br>Initials* | Cite<br>No. <sup>1</sup> | Document Number                          | Publication Date<br>MM-DD-YYYY | Name of Patentee or<br>Applicant of Cited Document | Pages, Columns, Lines, Where<br>Relevant Passages or Relevant<br>Figures Appear |
|                       |                          | Number/Kind Code <sup>2</sup> (if known) |                                |  |   |
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| Examiner<br>Initials*    | Cite<br>No. <sup>1</sup> | Foreign Patent Document   | Publication<br>Date<br>MM-DD-YYYY | Name of Patentee or<br>Applicant of Cited Document | Pages, Columns, Lines,<br>Where Relevant Passages<br>or Relevant Figures Appear | T <sup>4</sup> |
|                          |                          | Country Code <sup>3</sup> -Number-Kind Code <sup>2</sup> (if known) |                                   |  |   |                |
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| Examiner<br>Signature | Armando Rodriguez | Date<br>Considered | 3-27-06 |
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| Examiner<br>Signature | Amanda Rodriguez |  |                                | Date<br>Considered                                 | 3-31-06   |

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|   |   | Examiner Name            | A. Rodriguez           |
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| Examiner Signature | Armando Rodriguez | Date Considered | 3-31-06 |
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|   |   | First Named Inventor     | Joseph E. Geusic       |
|   |   | Art Unit                 | 2828                   |
|   |   | Examiner Name            | A. Rodriguez           |
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|   |   | Attorney Docket Number   | M4065.0439/P439        |

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| AL | AK5 | 2002/0079557 | 06/2002 | Ahn, et al.           |  |

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|   |   | Application Number       | 09/855,532-Conf. #9772 |
| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Use as many sheets as necessary) |   | Filing Date              | May 16, 2001           |
|   |   | First Named Inventor     | Joseph E. Geusic       |
|   |   | Art Unit                 | 2828                   |
|   |   | Examiner Name            | A. Rodriguez           |
| Sheet   | 5 | of                       | 10                     |
|   |   | Attorney Docket Number   | M4065.0439/P439        |

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|   |   | Examiner Name            | A. Rodriguez           |                        |                 |
| Sheet   | 6 | of                       | 10                     | Attorney Docket Number | M4065.0439/P439 |

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|   |   | Examiner Name            | A. Rodriguez           |
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| Date Considered    | 3-37-06           |  |

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| Examiner Signature |     | Armando Rodriguez  | Date Considered 3-31-06 |

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|   |    | Application Number       | 09/855,532-Conf. #9772 |
| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Use as many sheets as necessary) |    | Filing Date              | May 16, 2001           |
|   |    | First Named Inventor     | Joseph E. Geusic       |
|   |    | Art Unit                 | 2828                   |
|   |    | Examiner Name            | A. Rodriguez           |
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